PROCESS CP237

Small Signal Transistor

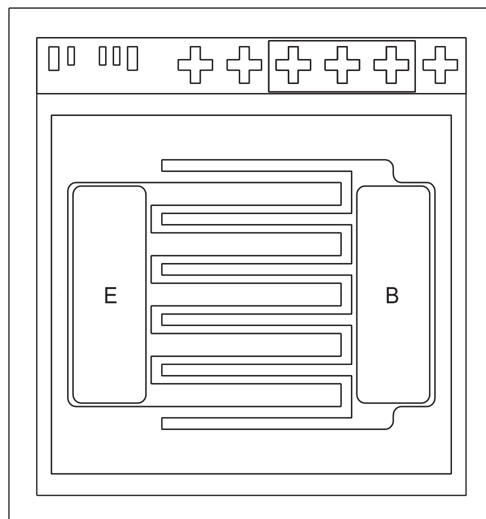
NPN - Saturated Switch Transistor Chip

Central™
Semiconductor Corp.

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	30 x 30 MILS
Die Thickness	9.0 MILS
Base Bonding Pad Area	4.4 x 12.5 MILS
Emitter Bonding Pad Area	4.4 x 12.5 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



R1

BACKSIDE COLLECTOR

GROSS DIE PER 4 INCH WAFER

12,550

PRINCIPAL DEVICE TYPES

2N3725
2N3725A
MPQ3725
MPQ3725A

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centralsemi.com

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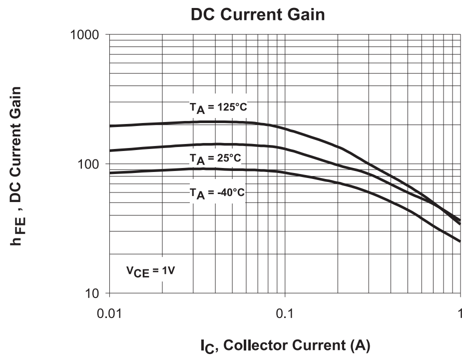
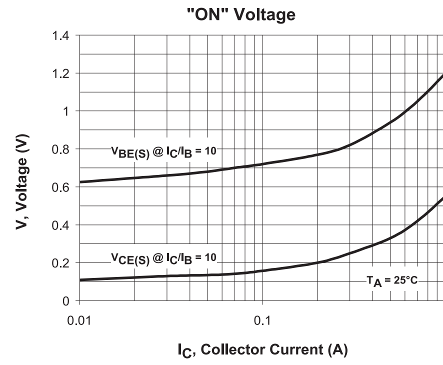
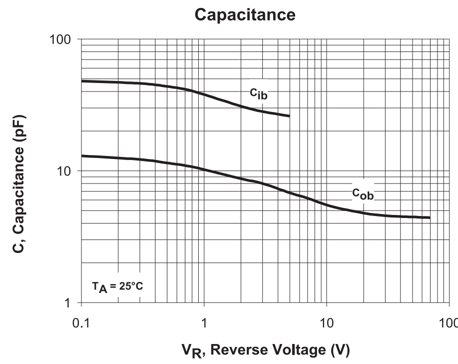
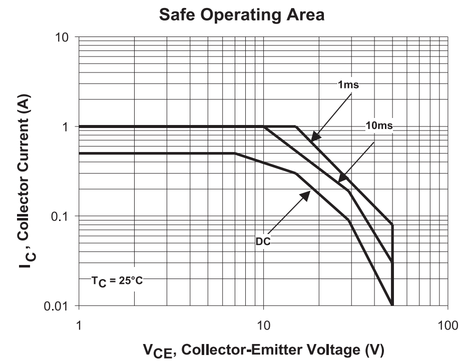
PROCESS CP237

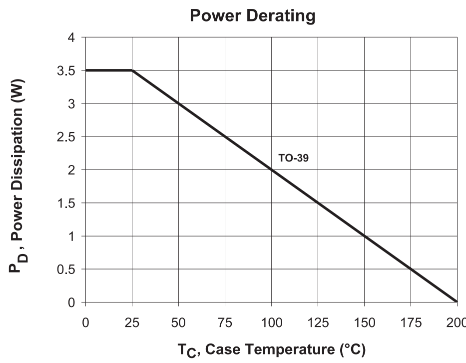
Typical Electrical Characteristics

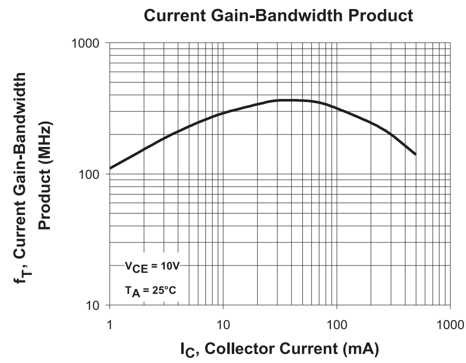












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